

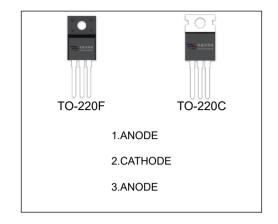
# MUR1060CT , MURF1060CT SUPER FAST

## MAIN CHARACTERISTICS

Io	10A
$V_{RRM}$	600 V
T <sub>j</sub>	150 ℃
V <sub>F(typ)</sub>	1.3V (@Tj=125℃)

#### **FEATURES**

- Ultrafast 35ns Recovery Times
- High Voltage Capability to 600V
- Low Reverse Leakage Current



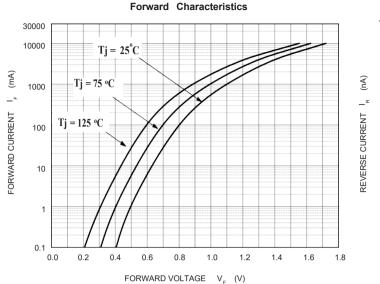
## MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

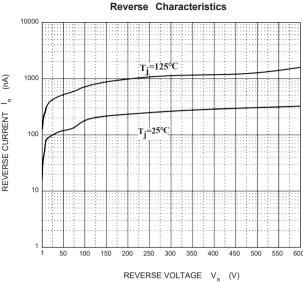
Cumahad	Davamatav	M	MUR		
Symbol	Parameter	1060CT	F1060CT	Unit	
V <sub>RRM</sub>	Peak repetitive reverse voltage				
V <sub>RWM</sub>	Working peak reverse voltage	6	600		
V <sub>R</sub>	DC blocking voltage				
V <sub>R(RMS)</sub>	RMS reverse voltage	4	420		
	Average rectified output current@ Per leg		5		
I <sub>o</sub> Average recti	Average rectified output current@ Total device		10		
	Non-Repetitive peak forward surge current		70		
I <sub>FSM</sub>	8.3ms half sine wave	,	70		
$\mathbf{P}_{D}$	Power dissipation		2		
R <sub>OJA</sub>	Thermal resistance from junction to ambient	6	62.5		
T <sub>j</sub>	Operating Junction Temperature Range	-55 ^	-55 ~ +150		
T <sub>stg</sub>	Storage Temperature Range	-55 ^	-55 ~ +150		

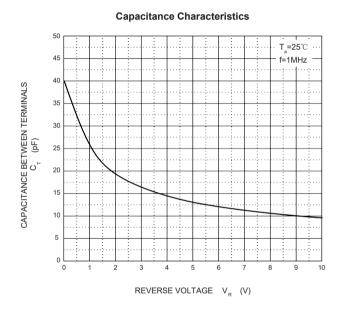
## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	I <sub>R</sub> =100uA		600			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =600V	Tj =25℃		0.5	2	uA
			Tj =125℃		2.0		uA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =5.0A	Tj =25℃		1.5	1.7	V
			Tj =125℃		1.3		V
Typical total capacitance	C <sub>tot</sub>	V <sub>R</sub> =4.0V,f=1MHz			14		pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5A, I <sub>R</sub> =1A,I <sub>rr</sub> =0.25A				35	ns









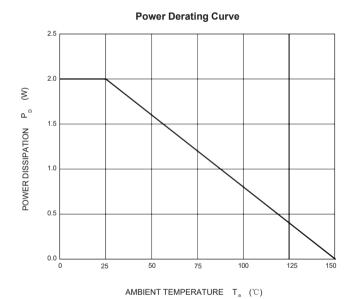


Diagram of circuit and Testing wave form of reverse recovery time

